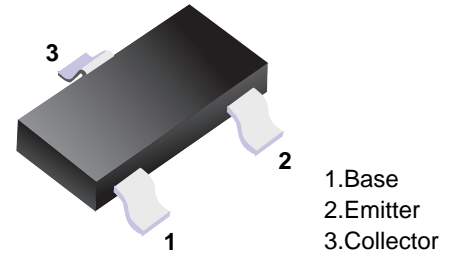


■ PNP Transistors

■ Features

- Ideal for Medium Power Amplification and Switching
- Complementary NPN Type Available (MMBT4401)



■ Simplified outline(SOT-23)

■ Marking

Marking	2T
---------	----

■ Absolute Maximum Ratings Ta = 25°C

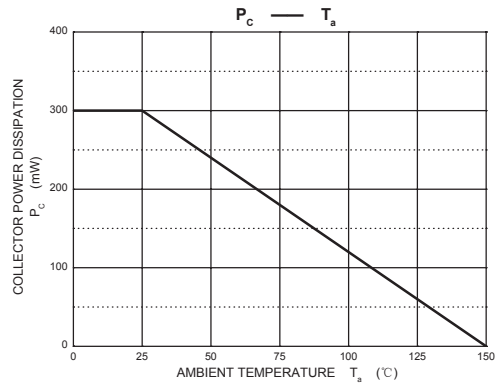
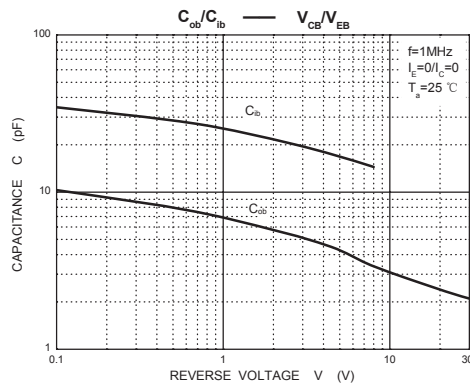
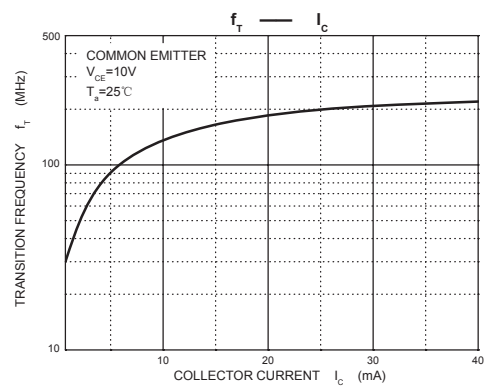
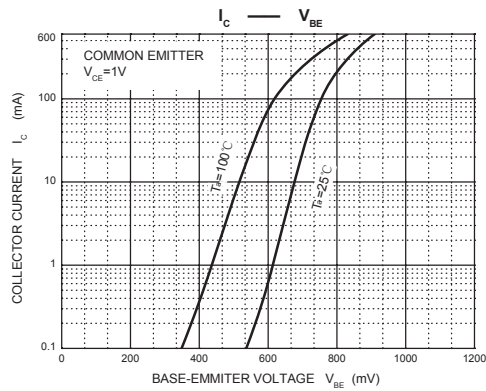
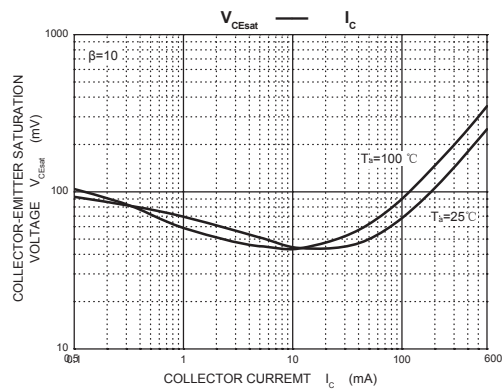
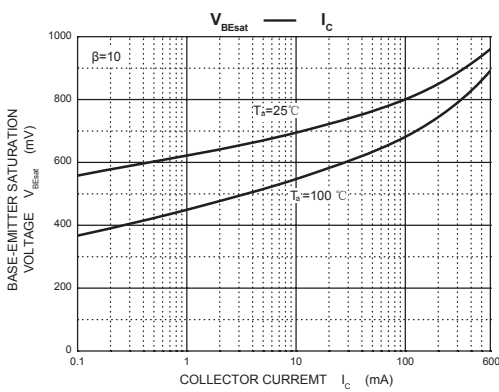
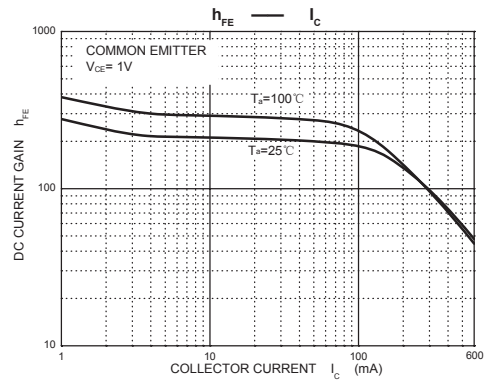
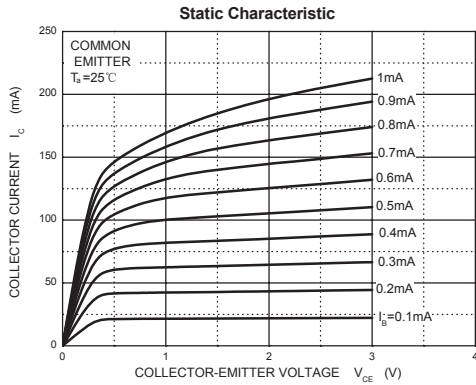
Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CB0}	-40	V
Collector-emitter voltage	V _{CEO}	-40	V
Emitter-base voltage	V _{EBO}	-5	V
Collector current	I _C	-600	mA
Total Device Dissipation Alumina Substrate	P _D	300	mW
Thermal Resistance, Junction to Ambient	R _{θJA}	417	°C/W
Junction and Storage Temperature	T _J , T _{stg}	-55 to150	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C = 100μA, I _E = 0	-40			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C = 1.0 mA, I _B = 0	-40			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E = 100μA, I _C = 0	-5			V
Collector cut-off current	I _{CBO}	V _{CB} = -35 V, I _E = 0			-0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} = -4V, I _C = 0			-0.1	μA
DC current gain *	h _{FE}	I _C = -0.1 mA, V _{CE} = -1.0 V	30			
		I _C = -1.0 mA, V _{CE} = -1.0 V	60			
		I _C = -10 mA, V _{CE} = -1.0 V	100			
		I _C = -150 mA, V _{CE} = -2.0 V	100		300	
		I _C = -500 mA, V _{CE} = -2.0 V	20			
Collector-emitter saturation voltage *	V _{CE(sat)}	I _C = -150 mA, I _B = -15 mA			-0.4	V
		I _C = -500 mA, I _B = -50 mA			-0.75	
Base-emitter saturation voltage *	V _{BE(sat)}	I _C = 150 mA, I _B = 15 mA	-0.75		-0.95	V
		I _C = 500 mA, I _B = 50 mA			-1.3	
Transition frequency	f _T	I _C = 20 mA, V _{CE} = 10 V, f = 100 MHz	200			MHz
Delay time	t _d	V _{CC} = 30 V, V _{EB} = 2.0 V,			15	ns
Rise time	t _r	I _C = 150 mA, I _{B1} = 15 mA			20	ns
Storage time	t _s	V _{CC} = 30 V, I _C = 150 mA,			225	ns
Fall time	t _f	I _{B1} = I _{B2} = 15 mA			30	ns

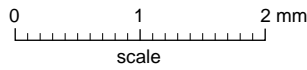
* Pulse test: pulse width ≤ 300 μs, duty cycle ≤ 2.0%.

■ Typical Characteristics



Package Outline

SOT-23



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁ max.	b _p	c	D	E	e	e ₁	H _E	L _p	Q	v	w
mm	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1

Summary of Packing Options

Package	Packing Description	Packing Quantity	Industry Standard
SOT-23	Tape/Reel, 7" reel	3000	EIA-481-1

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for [Bipolar Transistors - BJT category](#):

Click to view products by [YFW Electronics manufacturer](#):

Other Similar products are found below :

[BC559C](#) [MCH4017-TL-H](#) [MMBT-2369-TR](#) [BC546/116](#) [NJVMJD148T4G](#) [NTE16](#) [NTE195A](#) [IMX9T110](#) [2N4401-A](#) [2N6728](#) [2SA1419T-TD-H](#) [2SA2126-E](#) [2SB1204S-TL-E](#) [FMC5AT148](#) [2N2369ADCSM](#) [2N2907A](#) [2N3904-NS](#) [2N5769](#) [2SC4618TLN](#) [CPH6501-TL-E](#) [MCH4021-TL-E](#) [US6T6TR](#) [BAX18/A52R](#) [BC556/112](#) [IMZ2AT108](#) [MMST8098T146](#) [UMX21NTR](#) [MCH6102-TL-E](#) [TTA1452B,S4X\(S](#) [2N3879](#) [NTE13](#) [NTE282](#) [NTE323](#) [NTE350](#) [NTE81](#) [JANTX2N2920L](#) [JANTX2N3735](#) [JANSR2N2222AUB](#) [CMLT3946EG TR](#) [SNSS40600CF8T1G](#) [2N6987](#) [CMLT3906EG TR](#) [GRP-DATA-JANS2N2907AUB](#) [GRP-DATA-JANS2N2222AUA](#) [MMDT3946FL3-7](#) [2N4240](#) [JANS2N3019](#) [MSB30KH-13](#) [2N2221AUB](#) [2SD1815T-TL-E](#)